

**Dual P-Ch 30V Fast Switching MOSFETs**
**Description**

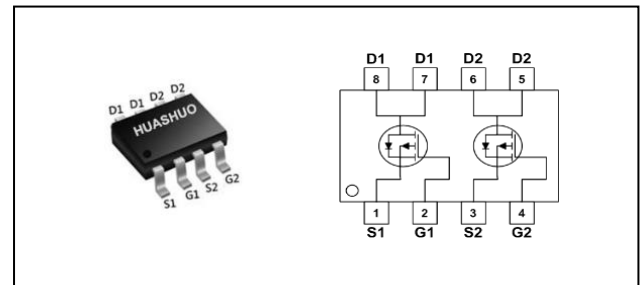
The HSM3305 is the high cell density trenched P-ch MOSFETs, which provide excellent R<sub>DS(ON)</sub> and gate charge for most of the synchronous buck converter applications.

The HSM3305 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

**Product Summary**

V <sub>DS</sub>	-30	V
R <sub>DS(ON),typ</sub>	42	mΩ
I <sub>D</sub>	-5	A

**SOP8 Pin Configuration**

**Absolute Maximum Ratings**

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	-30	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub> @T <sub>A</sub> =25°C	Continuous Drain Current, -V <sub>GS</sub> @ -10V <sup>1</sup>	-5	A
I <sub>D</sub> @T <sub>A</sub> =70°C	Continuous Drain Current, -V <sub>GS</sub> @ -10V <sup>1</sup>	-3.9	A
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	-20	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	50	mJ
I <sub>AS</sub>	Avalanche Current	-28	A
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation <sup>4</sup>	1.5	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C

**Thermal Data**

Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJA</sub>	Thermal Resistance Junction-Ambient <sup>1</sup>	---	78	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>	---	25	°C/W



**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-30	---	---	V
ΔBV <sub>DSS</sub> /ΔT <sub>J</sub>	BV <sub>DSS</sub> Temperature Coefficient	Reference to 25°C, I <sub>D</sub> =-1mA	---	-0.022	---	V/°C
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-4A	---	42	60	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-2A	---	62	90	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =-250uA	-1.0	1.5	-3	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	4.6	---	mV/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	-1	uA
		V <sub>DS</sub> =-24V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	-5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =-15V, I <sub>D</sub> =-5.3A	---	11	---	S
R <sub>g</sub>	Gate Resistance	V <sub>DS</sub> =0V, V <sub>GS</sub> =0V, f=1MHz	---	13	---	Ω
Q <sub>g</sub>	Total Gate Charge (-4.5V)	V <sub>DS</sub> =-15V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-3A	---	17	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	3	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	3.5	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =-15V, V <sub>GS</sub> =-10V, R <sub>L</sub> =5Ω, I <sub>D</sub> =-1A, R <sub>GEN</sub> =6Ω	---	10	---	ns
T <sub>r</sub>	Rise Time		---	6	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	46	---	
T <sub>f</sub>	Fall Time		---	23	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, f=1MHz	---	840	---	pF
C <sub>oss</sub>	Output Capacitance		---	175	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	125	---	

**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,5</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	-5	A
I <sub>SM</sub>	Pulsed Source Current <sup>2,5</sup>		---	---	-20	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =-1A, T <sub>J</sub> =25°C	---	---	-1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =-6A, dI/dt=100A/μs, T <sub>J</sub> =25°C	---	16.3	---	nS
Q <sub>rr</sub>	Reverse Recovery Charge		---	5.9	---	nC

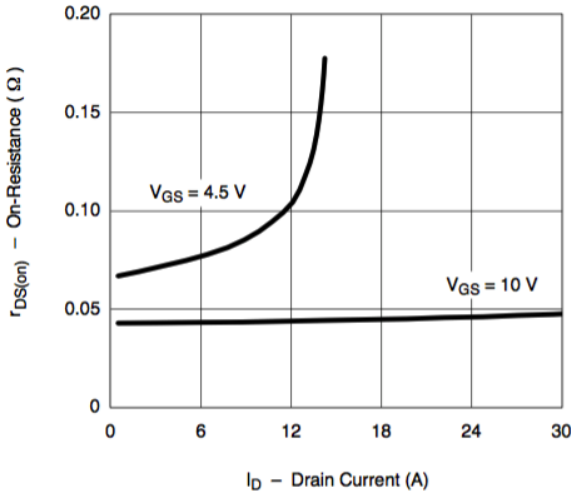
Note :

- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
- 3.The EAS data shows Max. rating. The test condition is V<sub>DD</sub>=-25V, V<sub>GS</sub>=-10V, L=0.1mH, I<sub>AS</sub>=-20A
- 4.The power dissipation is limited by 150°C junction temperature
- 5.The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub>, in real applications, should be limited by total power dissipation.

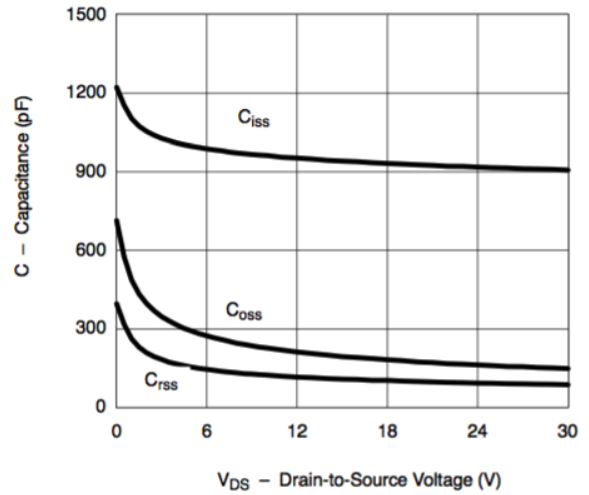


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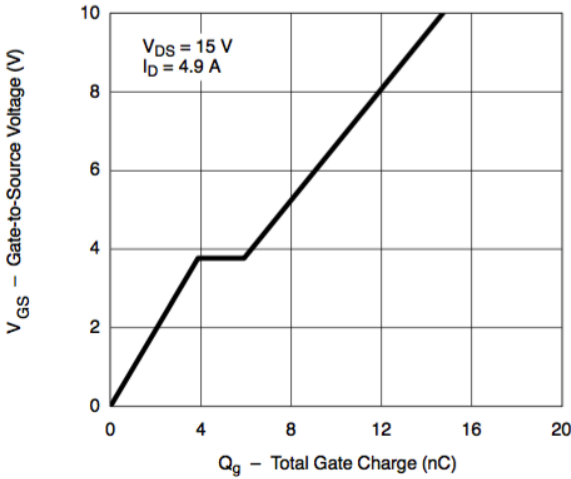
**On-Resistance vs. Drain Current**



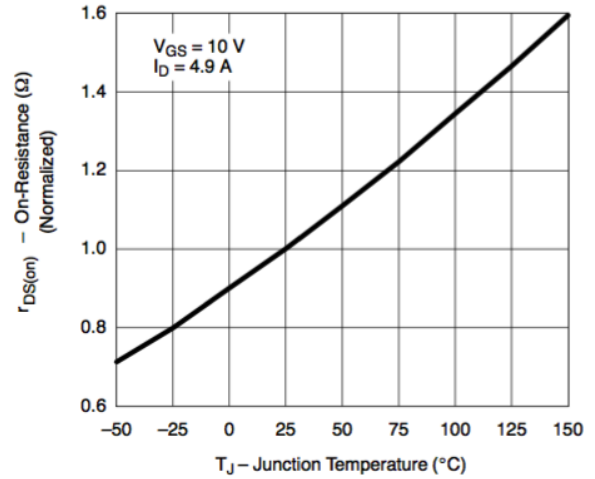
**Capacitance**



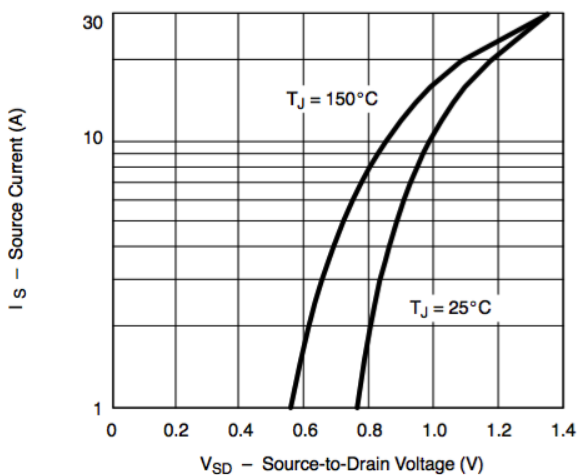
**Gate Charge**



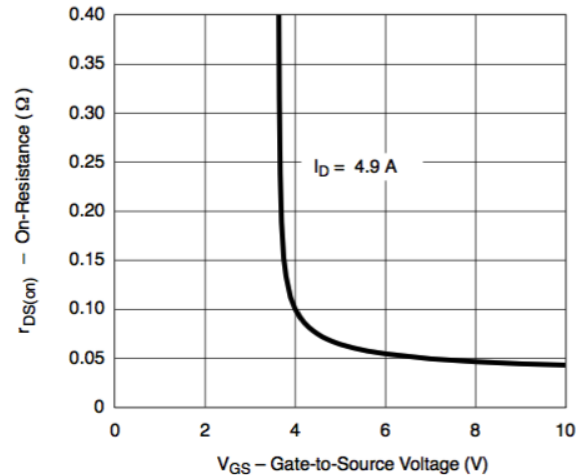
**On-Resistance vs. Junction Temperature**



**Source-Drain Diode Forward Voltage**



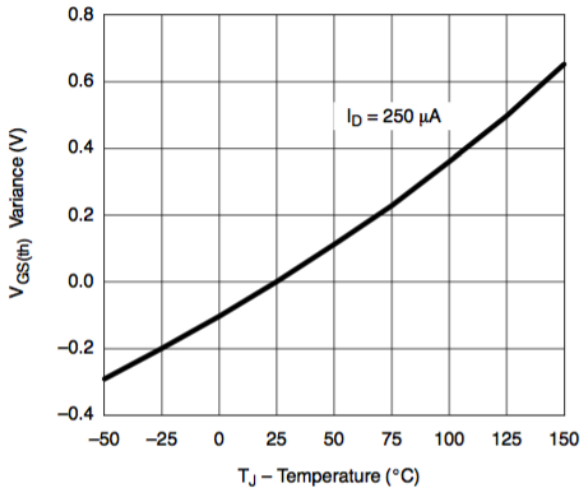
**On-Resistance vs. Gate-to-Source Voltage**



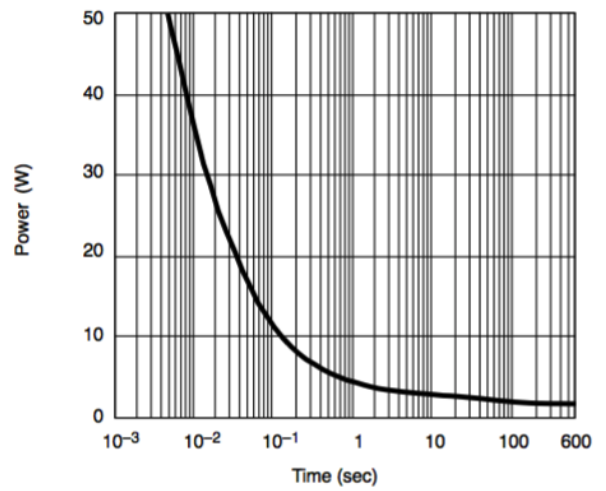


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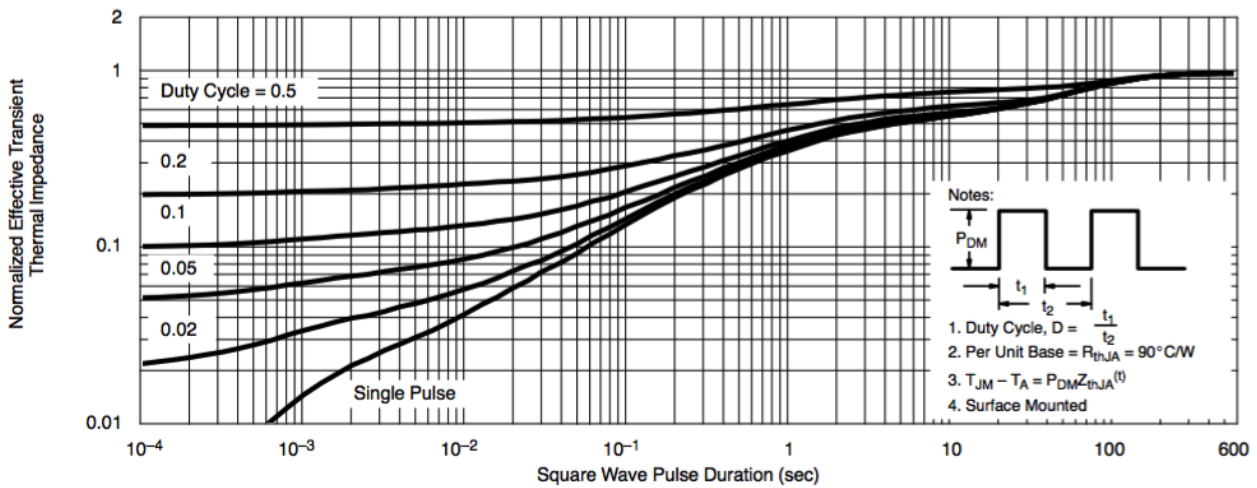
**Threshold Voltage**



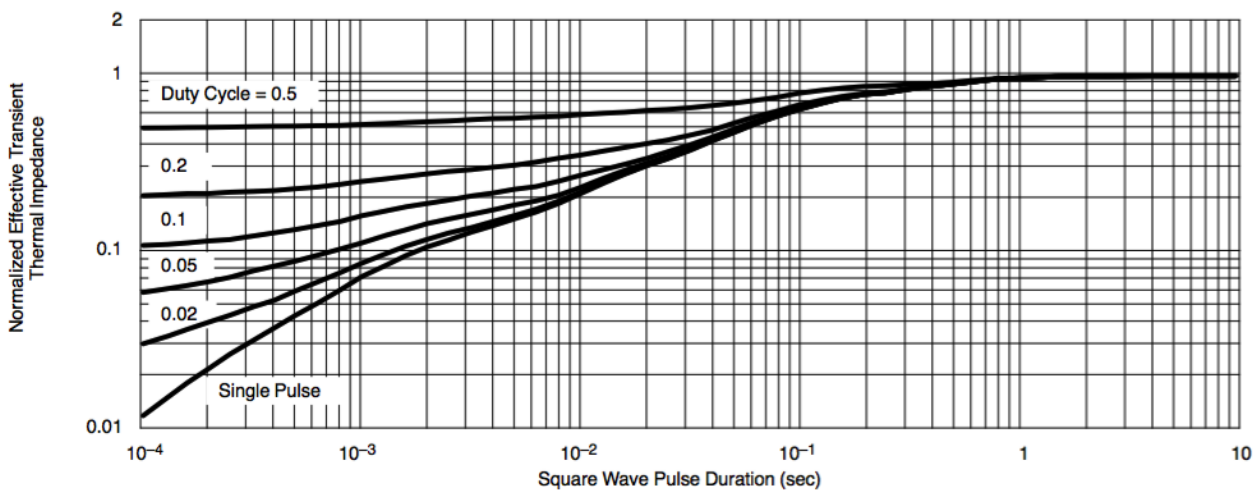
**Single Pulse Power**



**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**Normalized Thermal Transient Impedance, Junction-to-Foot**





## Ordering Information

Part Number	Package code	Packaging
HSM3305	SOP-8	4000/Tape&Reel

